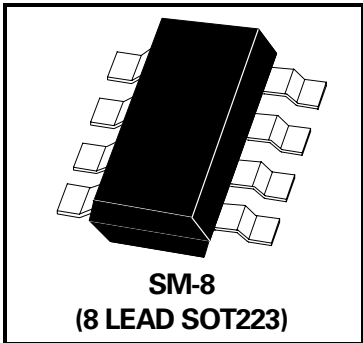
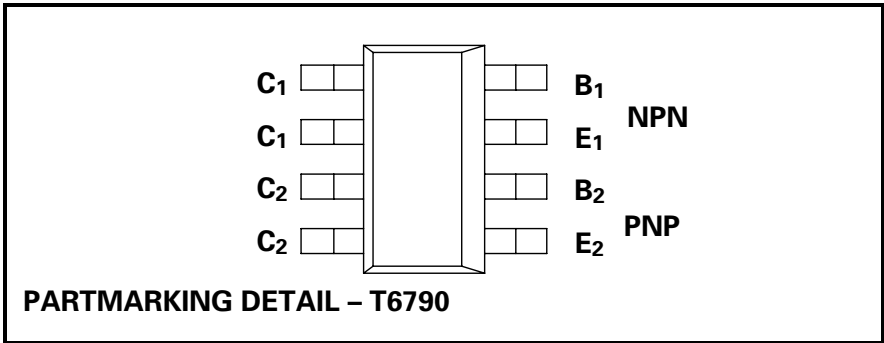


SM-8 COMPLEMENTARY MEDIUM POWER HIGH GAIN TRANSISTORS

ISSUE 1 - NOVEMBER 1995

ZDT6790



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	NPN	PNP	UNIT
Collector-Base Voltage	V _{CBO}	45	-50	V
Collector-Emitter Voltage	V _{CEO}	45	-40	V
Emitter-Base Voltage	V _{EBO}	5	-5	V
Peak Pulse Current	I _{CM}	6	-6	A
Continuous Collector Current	I _C	2	-2	A
Operating and Storage Temperature Range	T _j ; T _{stg}	-55 to +150		°C

THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	VALUE	UNIT
Total Power Dissipation at T _{amb} = 25°C* Any single die "on" Both die "on" equally	P _{tot}	2.25	W
		2.75	W
Derate above 25°C* Any single die "on" Both die "on" equally		18	mW/°C
		22	mW/°C
Thermal Resistance - Junction to Ambient* Any single die "on" Both die "on" equally		55.6	°C/W
		45.5	°C/W

* The power which can be dissipated assuming the device is mounted in a typical manner on a PCB with copper equal to 2 inches square.

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NPN TRANSISTOR ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	45			V	$I_C=100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	45			V	$I_C=10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5			V	$I_E=100\mu\text{A}$
Collector Cutoff Current	I_{CBO}			0.1	μA	$V_{CB}=35\text{V}$
Emitter Cutoff Current	I_{EBO}			0.1	μA	$V_{EB}=4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.1 0.5	V V	$I_C=0.1\text{A}, I_B=0.5\text{mA}^*$ $I_C=1\text{A}, I_B=5\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			0.9	V	$I_C=1\text{A}, I_B=10\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			0.9	V	$I_C=1\text{A}, V_{CE}=2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	500 400 150				$I_C=100\text{mA}, V_{CE}=2\text{V}^*$ $I_C=1\text{A}, V_{CE}=2\text{V}^*$ $I_C=2\text{A}, V_{CE}=2\text{V}^*$
Transition Frequency	f_T	150			MHz	$I_C=50\text{mA}, V_{CE}=5\text{V}$ $f=50\text{MHz}$
Input Capacitance	C_{ibo}		200		pF	$V_{EB}=0.5\text{V}, f=1\text{MHz}$
Output Capacitance	C_{obo}		16		pF	$V_{CB}=10\text{V}, f=1\text{MHz}$
Switching Times	t_{on} t_{off}		33 1300		ns	$I_C=500\text{mA}, I_{B1}=50\text{mA}$ $I_{B2}=50\text{mA}, V_{CC}=10\text{V}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$
For typical characteristics graphs see FZT690 datasheet.

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PNP TRANSISTOR ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-50			V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-40			V	$I_C = -10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = -100\mu\text{A}$
Collector Cutoff Current	I_{CBO}			-0.1	μA	$V_{CB} = -30\text{V}$
Emitter Cutoff Current	I_{EBO}			-0.1	μA	$V_{EB} = -4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.25 -0.45 -0.75	V V V	$I_C = -500\text{mA}, I_B = -5\text{mA}^*$ $I_C = -1\text{A}, I_B = -10\text{mA}^*$ $I_C = -2\text{A}, I_B = -50\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-1.0	V	$I_C = -1\text{A}, I_B = -10\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-0.75		V	$I_C = -1\text{A}, V_{CE} = -2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	300 250 200 150		800		$I_C = -10\text{mA}, V_{CE} = -2\text{V}$ $I_C = -500\text{mA}, V_{CE} = -2\text{V}^*$ $I_C = -1\text{A}, V_{CE} = -2\text{V}^*$ $I_C = -2\text{A}, V_{CE} = -2\text{V}^*$
Transition Frequency	f_T	100			MHz	$I_C = -50\text{mA}, V_{CE} = -5\text{V}$ $f = 50\text{MHz}$
Input Capacitance	C_{ibo}		225		pF	$V_{EB} = -0.5\text{V}, f = 1\text{MHz}$
Output Capacitance	C_{obo}		24		pF	$V_{CB} = -10\text{V}, f = 1\text{MHz}$
Switching Times	t_{on} t_{off}		35 600		ns	$I_C = -500\text{mA},$ $I_{B1} = -50\text{mA}$ $I_{B2} = -50\text{mA}, V_{CC} = -10\text{V}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$
For typical characteristics graphs see FZT790 datasheet.